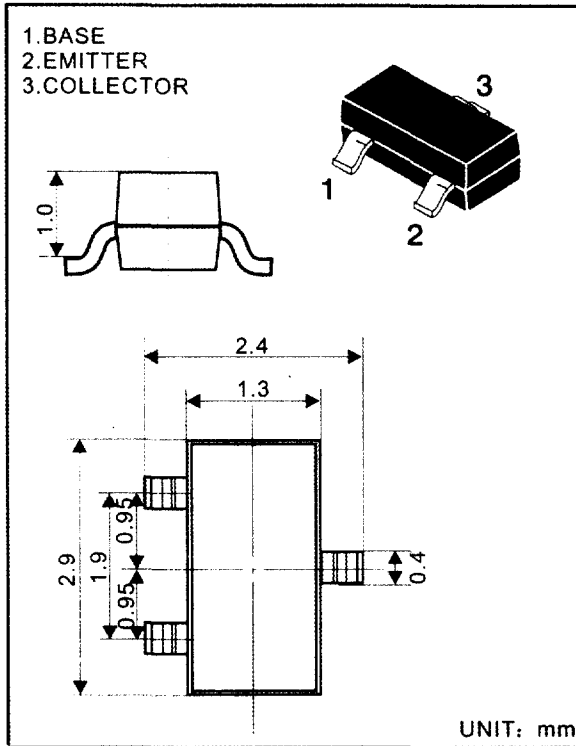


# SOT-23 Plastic-Encapsulate Transistors

## MMBT3906LT1 TRANSISTOR (PNP)



### FEATURES

**Power dissipation**

PCM: 0.2 W (Tamb=25°C)

**Collector current**

ICM: -0.2 A

**Collector-base voltage**

V(BR)CBO: -40V

**Operating and storage junction temperature range**

TJ, Tstg : -55°C to +150°C

### ELECTRICAL CHARACTERISTICS

(Tamp=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX
Collector-base breakdown voltage	V(BR)CBO	IC=-100 μA, IE=0	-40		V
Collector-emitter breakdown voltage	V(BR)CEO	IC=-1mA, IB=0	-40		V
Emitter-base breakdown voltage	V(BR)EBO	IC=-100 μA, IB=0	-5		V
Collector cut-off current	ICBO	VCB=-40V, IE=0			-0.1 μA
Collector cut-off current	ICEO	VCE=-40V, IB=0			-0.1 μA
Emitter cut-off current	IEBO	VEB=-5V, IC=0mA			-0.1 μA
DC current gain	hFE(1)	VCE=-1V, IC= -10mA	100	300	
	hFE(2)	VCE=-1V, IC=-50mA	60		
Collector-emitter saturation voltage	VCEsat	IC=-50mA, IB=-5mA			-0.4 V
Base-emitter saturation voltage	VBEsat	IC=-50mA, IB=-5mA			-0.95 V
Transition frequency	ft	VCE=-20V, IC=-10mA, f=100MHz	250		MHz

DEVICE MARKING : MMBT3906LT1=2A

# Typical Characteristics

# MMBT3906LT1

